



# Z0107MA0

4Q Triac

23 August 2013

Product data sheet

## 1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT54 (TO-92) plastic package intended for use in applications requiring enhanced noise immunity and direct interfacing to logic ICs and low power gate drivers.

## 2. Features and benefits

- Direct interfacing to logic level ICs
- Enhanced current surge capability
- Enhanced noise immunity
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate

## 3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- Low power AC Fan controllers

## 4. Quick reference data

Table 1. Quick reference data

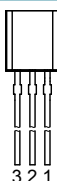
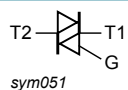
| Symbol                        | Parameter                            | Conditions   | Min | Typ | Max  | Unit |
|-------------------------------|--------------------------------------|--|-----|-----|------|------|
| $V_{\text{DRM}}$              | repetitive peak off-state voltage    |  | -   | -   | 600  | V    |
| $I_{\text{TSM}}$              | non-repetitive peak on-state current | full sine wave; $T_{\text{J}(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | -   | 12.5 | A    |
| $I_{\text{T(RMS)}}$           | RMS on-state current                 | full sine wave; $T_{\text{lead}} \leq 45\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>               | -   | -   | 1    | A    |
| <b>Static characteristics</b> |                                      |  |     |     |      |      |
| $I_{\text{GT}}$               | gate trigger current                 | $V_{\text{D}} = 12\text{ V}$ ; $I_{\text{T}} = 0.1\text{ A}$ ; T2+ G+; $T_{\text{J}} = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                | 0.3 | -   | 5    | mA   |
|                               |                                      | $V_{\text{D}} = 12\text{ V}$ ; $I_{\text{T}} = 0.1\text{ A}$ ; T2+ G-; $T_{\text{J}} = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                | 0.3 | -   | 5    | mA   |



| Symbol | Parameter | Conditions  | Min | Typ | Max | Unit |
|--------|-----------|---|-----|-----|-----|------|
|        |           | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a> | 0.3 | -   | 5   | mA   |
|        |           | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a> | 0.3 | -   | 7   | mA   |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description     | Simplified outline   | Graphic symbol  |
|-----|--------|-----------------|--|---|
| 1   | T2     | main terminal 2 |  <p>TO-92 (SOT54)</p> |  <p>sym051</p> |
| 2   | G      | gate            |  |   |
| 3   | T1     | main terminal 1 |  |   |

## 6. Ordering information

Table 3. Ordering information

| Type number | Package |   |         |
|-------------|---------|---|---------|
|             | Name    | Description   | Version |
| Z0107MA0    | TO-92   | plastic single-ended leaded (through hole) package; 3 leads | SOT54   |

## 7. Limiting values

**Table 4. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol              | Parameter                            | Conditions  |  | Min | Max  | Unit                   |
|---------------------|--------------------------------------|---|--|-----|------|------------------------|
| $V_{\text{DRM}}$    | repetitive peak off-state voltage    |   |  | -   | 600  | V                      |
| $I_{\text{T(RMS)}}$ | RMS on-state current                 | full sine wave; $T_{\text{lead}} \leq 45\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>        |  | -   | 1    | A                      |
| $I_{\text{TSM}}$    | non-repetitive peak on-state current | full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> |  | -   | 12.5 | A                      |
|                     |                                      | full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 16.7\text{ ms}$   |  | -   | 13.8 | A                      |
| $I^2t$              | $I^2t$ for fusing                    | $t_{\text{p}} = 10\text{ ms}$ ; SIN   |  | -   | 0.78 | $\text{A}^2\text{s}$   |
| $dl_{\text{T}}/dt$  | rate of rise of on-state current     | $I_{\text{T}} = 1\text{ A}$ ; $I_{\text{G}} = 20\text{ mA}$ ; $dl_{\text{G}}/dt = 100\text{ mA}/\mu\text{s}$ ; T2+ G+                               |  | -   | 50   | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{T}} = 1\text{ A}$ ; $I_{\text{G}} = 20\text{ mA}$ ; $dl_{\text{G}}/dt = 100\text{ mA}/\mu\text{s}$ ; T2+ G-                               |  | -   | 50   | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{T}} = 1\text{ A}$ ; $I_{\text{G}} = 20\text{ mA}$ ; $dl_{\text{G}}/dt = 100\text{ mA}/\mu\text{s}$ ; T2- G-                               |  | -   | 50   | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{T}} = 1\text{ A}$ ; $I_{\text{G}} = 20\text{ mA}$ ; $dl_{\text{G}}/dt = 100\text{ mA}/\mu\text{s}$ ; T2- G+                               |  | -   | 20   | $\text{A}/\mu\text{s}$ |
| $I_{\text{GM}}$     | peak gate current                    |   |  | -   | 1    | A                      |
| $P_{\text{GM}}$     | peak gate power                      |   |  | -   | 2    | W                      |
| $P_{\text{G(AV)}}$  | average gate power                   | over any 20 ms period   |  | -   | 0.1  | W                      |
| $T_{\text{stg}}$    | storage temperature                  |   |  | -40 | 150  | $^{\circ}\text{C}$     |
| $T_{\text{j}}$      | junction temperature                 |   |  | -   | 125  | $^{\circ}\text{C}$     |

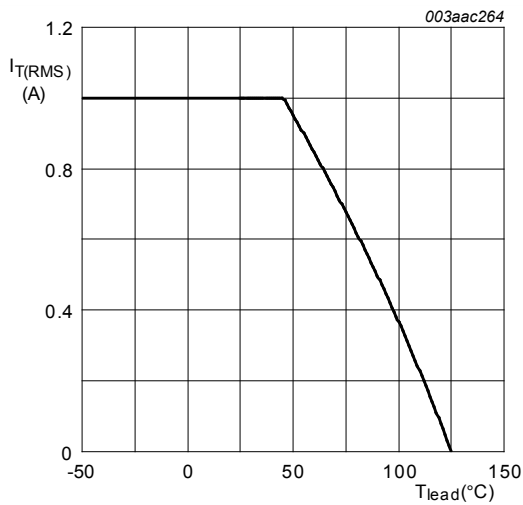
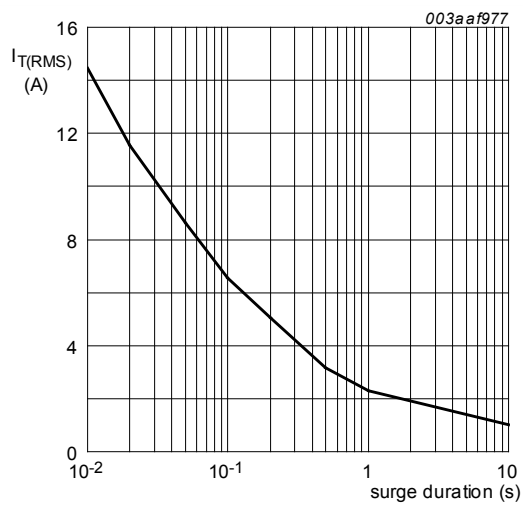


Fig. 1. RMS on-state current as a function of lead temperature; maximum values



f = 50 Hz;  $T_{lead}$  = 45 °C

Fig. 2. RMS on-state current as a function of surge duration; maximum values

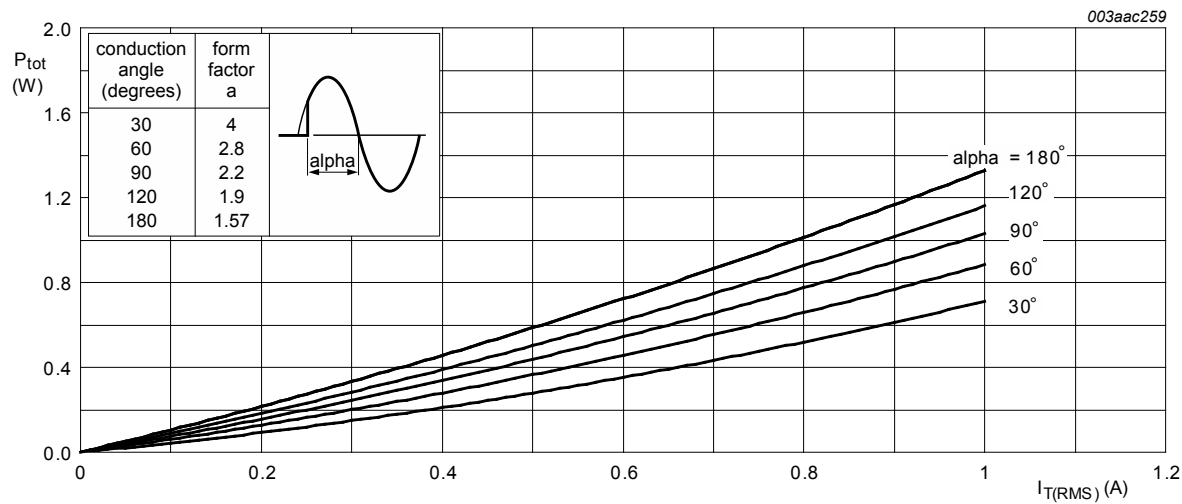
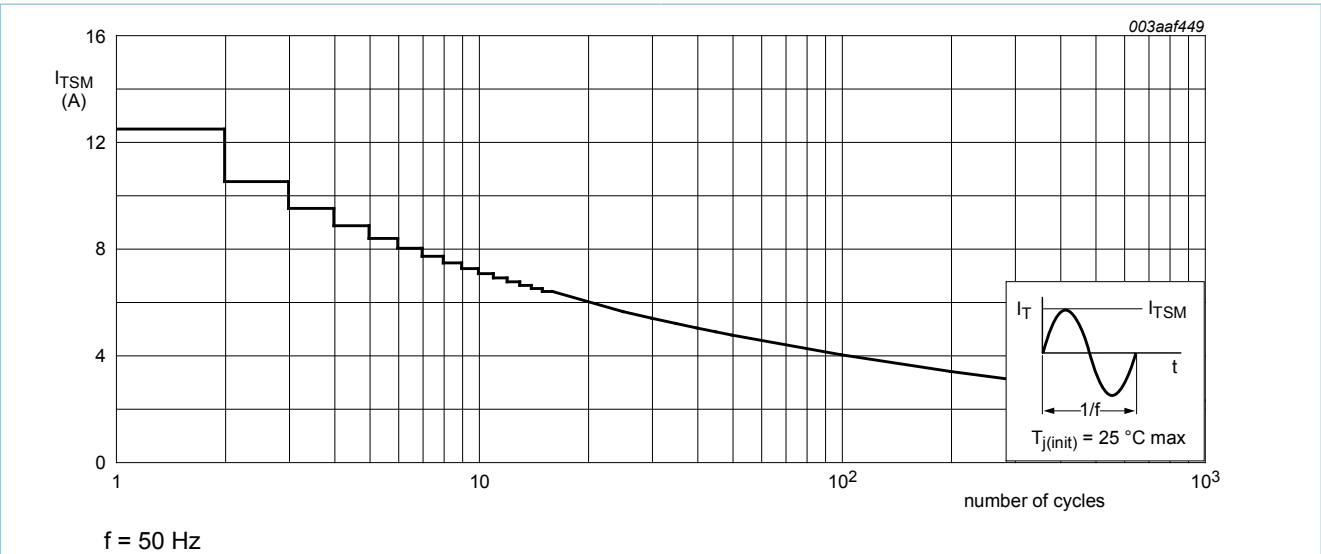
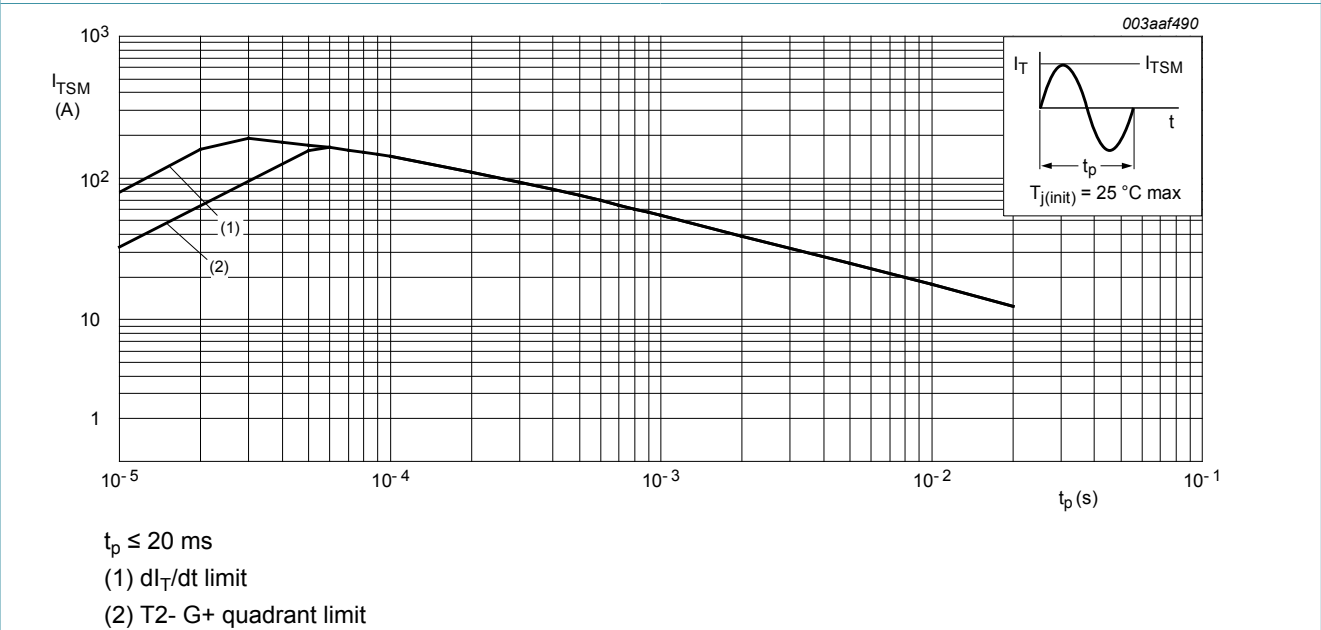


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



**Fig. 4.** Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



**Fig. 5.** Non-repetitive peak on-state current as a function of pulse width; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol           | Parameter                                   | Conditions  |  | Min | Typ | Max | Unit |
|------------------|---|---|--|-----|-----|-----|------|
| $R_{th(j-lead)}$ | thermal resistance from junction to lead    | full cycle; <a href="#">Fig. 6</a>                          |  | -   | -   | 60  | K/W  |
| $R_{th(j-a)}$    | thermal resistance from junction to ambient | full cycle; printed circuit board mounted; lead length 4 mm |  | -   | 150 | -   | K/W  |

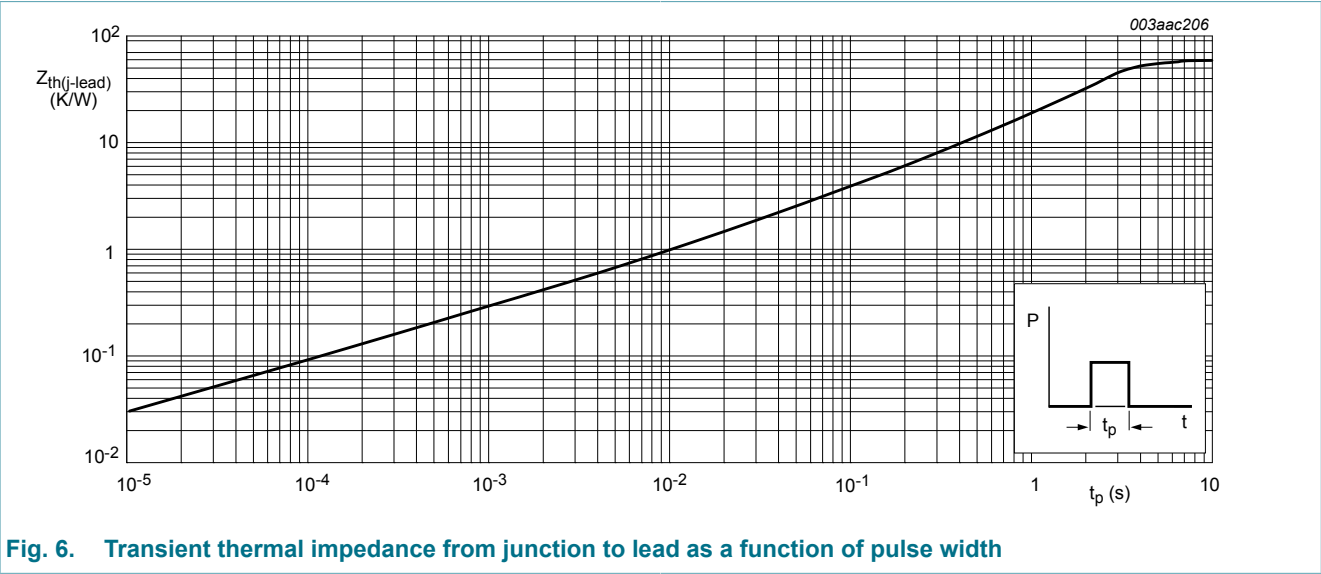
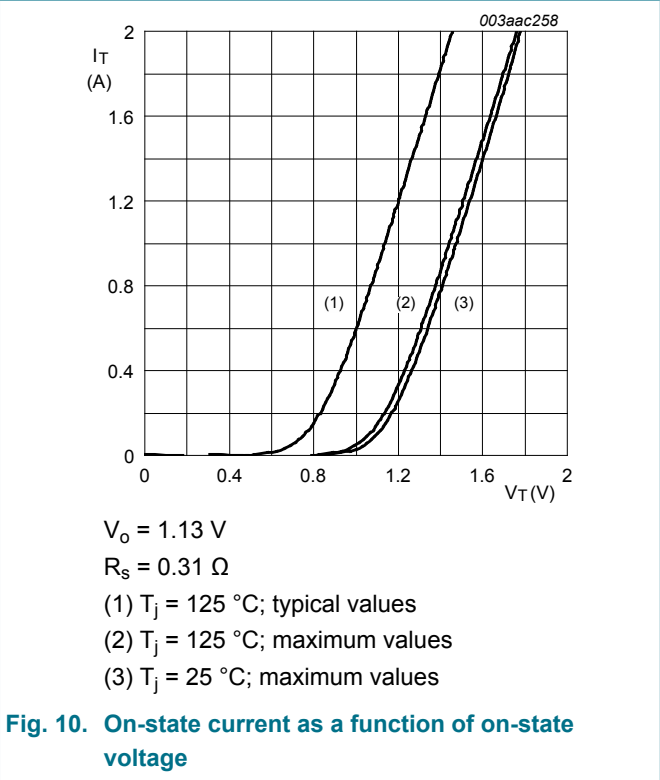
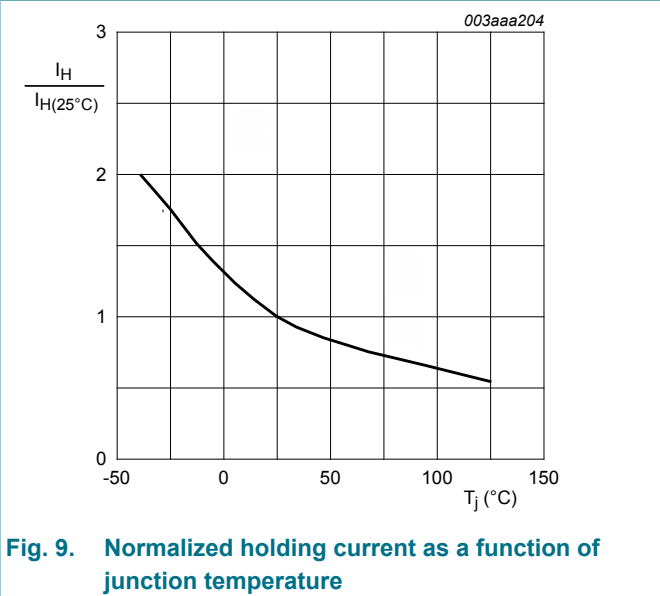
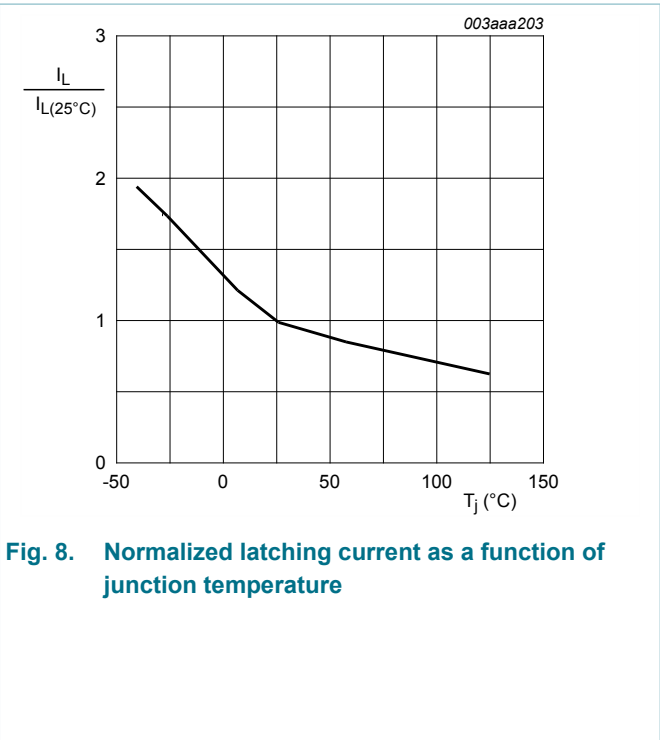
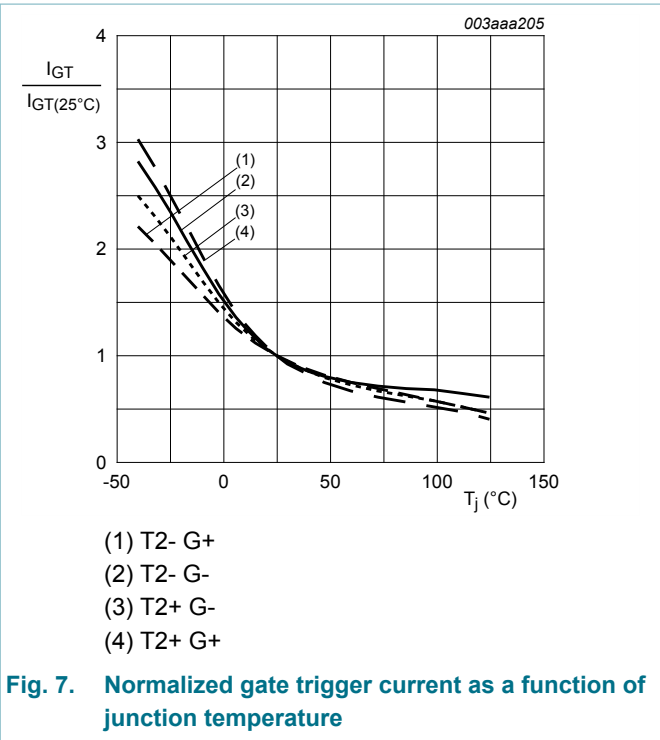


Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

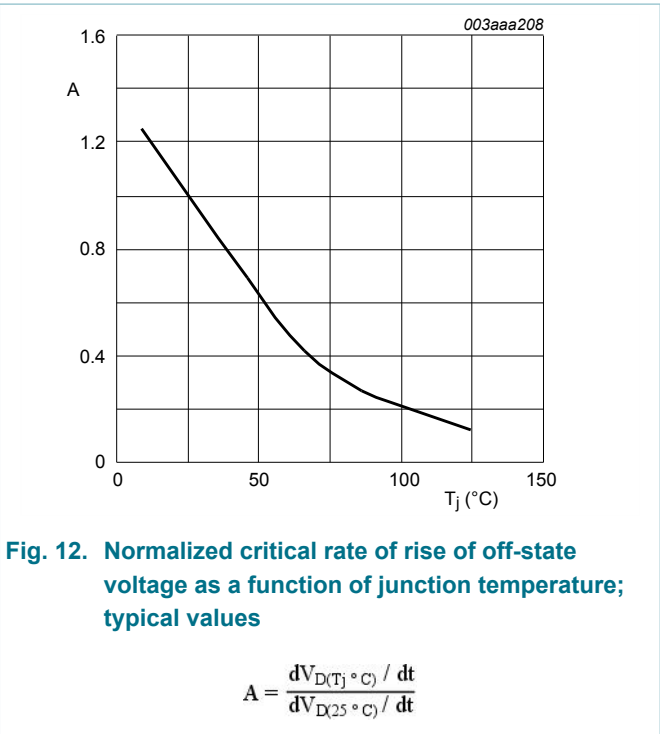
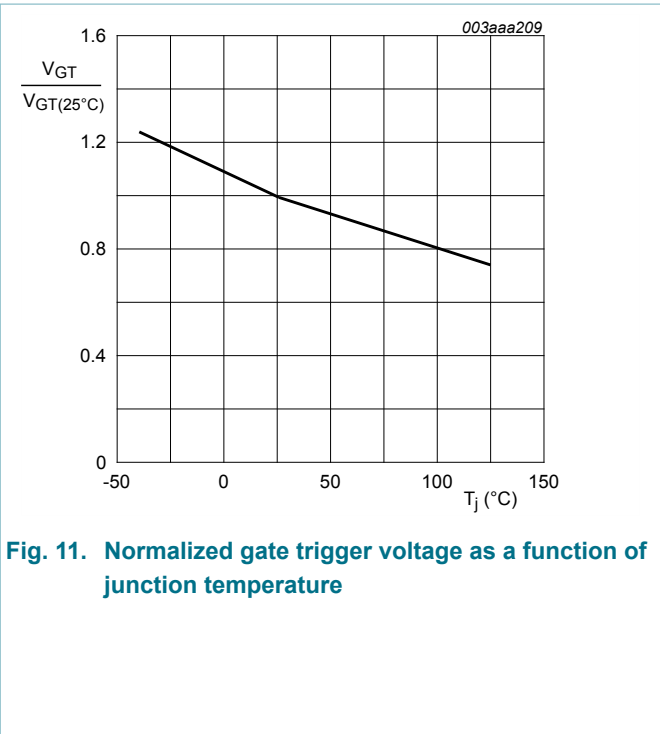
## 9. Characteristics

Table 6. Characteristics

| Symbol                         | Parameter                             | Conditions   | Min | Typ | Max | Unit             |
|--------------------------------|---------------------------------------|--|-----|-----|-----|------------------|
| <b>Static characteristics</b>  |                                       |  |     |     |     |                  |
| $I_{GT}$                       | gate trigger current                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>  | 0.3 | -   | 5   | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>  | 0.3 | -   | 5   | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>  | 0.3 | -   | 5   | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>  | 0.3 | -   | 7   | mA               |
| $I_L$                          | latching current                      | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>  | -   | -   | 10  | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>  | -   | -   | 25  | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>  | -   | -   | 10  | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>  | -   | -   | 10  | mA               |
| $I_H$                          | holding current                       | $V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>  | -   | -   | 10  | mA               |
| $V_T$                          | on-state voltage                      | $I_T = 1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>  | -   | 1.3 | 1.6 | V                |
| $V_{GT}$                       | gate trigger voltage                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 11</a>   | -   | -   | 1   | V                |
|                                |                                       | $V_D = 600\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 11</a>   | 0.2 | -   | -   | V                |
| $I_D$                          | off-state current                     | $V_D = 600\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$   | -   | -   | 0.5 | mA               |
| <b>Dynamic characteristics</b> |                                       |  |     |     |     |                  |
| $dV_D/dt$                      | rate of rise of off-state voltage     | $V_{DM} = 402\text{ V}$ ; $T_j = 110\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 12</a> | 100 | -   | -   | V/ $\mu\text{s}$ |
| $dV_{com}/dt$                  | rate of change of commutating voltage | $V_D = 400\text{ V}$ ; $T_j = 110\text{ }^\circ\text{C}$ ; $dI_{com}/dt = 0.44\text{ A/ms}$ ; gate open circuit  | 1   | -   | -   | V/ $\mu\text{s}$ |







# 10. Package outline

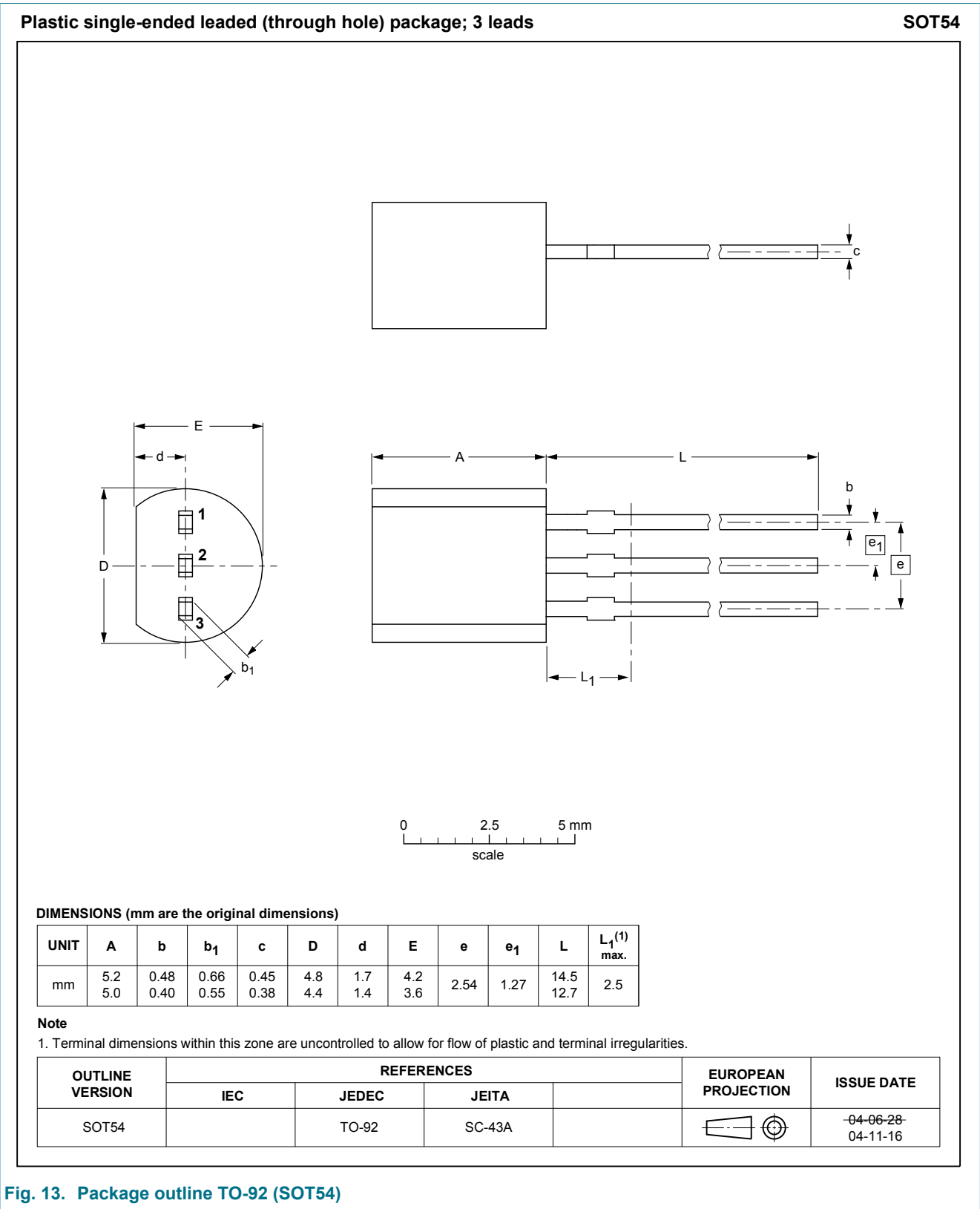


Fig. 13. Package outline TO-92 (SOT54)

## 11. Legal information

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|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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